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Inclosure Material:

Metal

Overall Length:

1.218 inches

Overall Diameter:

0.380 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact-darlington connected

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-111

Mounting Method:

Threaded stud

Overall Width Across Flats:

Between 0.424 inches and 0.437 inches

Thread Size:

0.190 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

60.0 breakdown voltage, collector-to-base, emitter open and 40.0 breakdown voltage, collector-to-emitter, base open and 15.0

breakdown voltage, emitter-to-base, collector open

Current Rating Per Characteristic:

3.00 amperes source cutoff current

Power Rating Per Characteristic:

12.5 watts small-signal input power, common-collector

Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: npn

Test Data Document:

82577-928399 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Thread Series Designator:

Unf

Terminal Type And Quantity:

4 tab, solder lug

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

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